Contents

Selection Guide

Description		-10	-12	-15	Unit
Maximum Access Time		10	12	15	ns
Maximum Operating Current	Automotive-A	100	95	–	mA
	Automotive-E	–	–	95	mA
Maximum CMOS Standby Current	Automotive-A	10	10	–	mA
	Automotive-E	–	–	15	mA

Pin Configuration

Figure 1. 36-pin SOJ pinout (Top View)

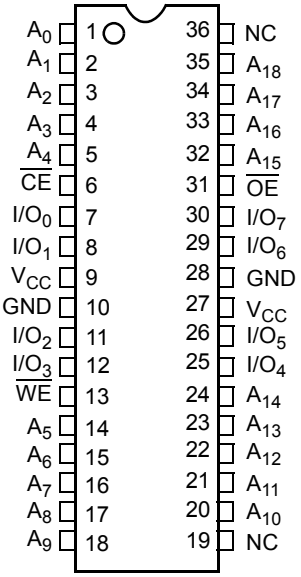
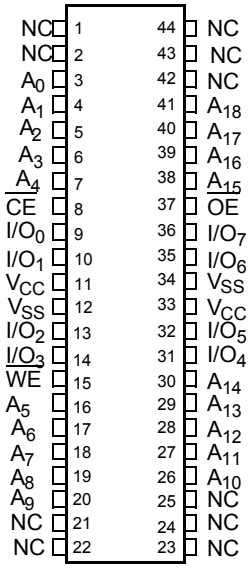


Figure 2. 44-pin TSOP II pinout (Top View)



Pin Definitions

Pin Name	36-pin SOJ Pin Number	44-pin TSOP II Pin Number	I/O Type	Description
A_0–A_{18}	1–5, 14–18, 20–24, 32–35	3–7, 16–20, 26–30, 38–41	Input	**Address inputs used to select one of the address locations**.
I/O_0–I/O_7	7, 8, 11, 12, 25, 26, 29, 30	9, 10, 13, 14, 31, 32, 35, 36	Input/Output	**Bidirectional data I/O lines**. Used as input or output lines depending on operation.
NC[1]	19, 36	1, 2, 21, 22, 23, 24, 25, 42, 43, 44	No Connect	**No connects**. This pin is not connected to the die.
$\overline{WE}$	13	15	Input/Control	**Write Enable input, active LOW**. When selected LOW, a WRITE is conducted.
$\overline{CE}$	6	8	Input/Control	**Chip Enable input, active LOW**. When LOW, selects the chip. When HIGH, deselects the chip.
$\overline{OE}$	31	37	Input/Control	**Output Enable, active LOW**. Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are tri-state, and act as input data pins.
V_{SS}, GND	10, 28	12, 34	Ground	**Ground for the device**. Should be connected to ground of the system.
V_{CC}	9, 27	11, 33	Power Supply	**Power supply inputs to the device**.

Note
1. NC pins are not connected on the die.

Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature ..... –65 °C to +150 °C

Ambient Temperature with Power Applied ..... –55 °C to +125 °C

Supply Voltage on V_{CC} to Relative GND [2] ..... –0.5 V to +4.6 VDC

Voltage Applied to Outputs in High Z State [2] ..... –0.5 V to V_{CC} + 0.5 V

Input Voltage [2] ..... –0.5 V to V_{CC} + 0.5 V

Current into Outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, Method 3015) ..... > 2001 V

Latch up current ..... > 200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Automotive-A	–40 °C to +85 °C	3.3 V ± 0.3 V
Automotive-E	–40 °C to +125 °C	

Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		-10		-12		-15		Unit
				Min	Max	Min	Max	Min	Max	
V_{OH}	Output HIGH Voltage	V_{CC} = Min; I_{OH} = –4.0 mA		2.4	–	2.4	–	2.4	–	V
V_{OL}	Output LOW Voltage	V_{CC} = Min; I_{OL} = 8.0 mA		–	0.4	–	0.4	–	0.4	V
V_{IH}	Input HIGH Voltage			2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	2.0	V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage[2]			–0.3	0.8	–0.3	0.8	–0.3	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}	Auto-A	–1	+1	–1	+1	–	–	µA
			Auto-E	–	–	–	–	–20	+20	
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max, f = f_{MAX} = $1/t_{RC}$	Auto-A	–	100	–	95	–	–	mA
			Auto-E	–	–	–	–	–	95	
I_{SB1}	Automatic CE Power Down Current – TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH}; V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}	Auto-A	–	40	–	40	–	–	mA
			Auto-E	–	–	–	–	–	45	mA
I_{SB2}	Automatic CE Power Down Current – CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3 V, V_{IN} ≥ V_{CC} – 0.3 V, or V_{IN} ≤ 0.3 V, f = 0	Auto-A	–	10	–	10	–	–	mA
			Auto-E	–	–	–	–	–	15	mA

Note
2. $V_{IL(min)}$ = –2.0 V and $V_{IH(max)}$ = V_{CC} + 0.5 V for pulse durations of less than 20 ns.

Capacitance

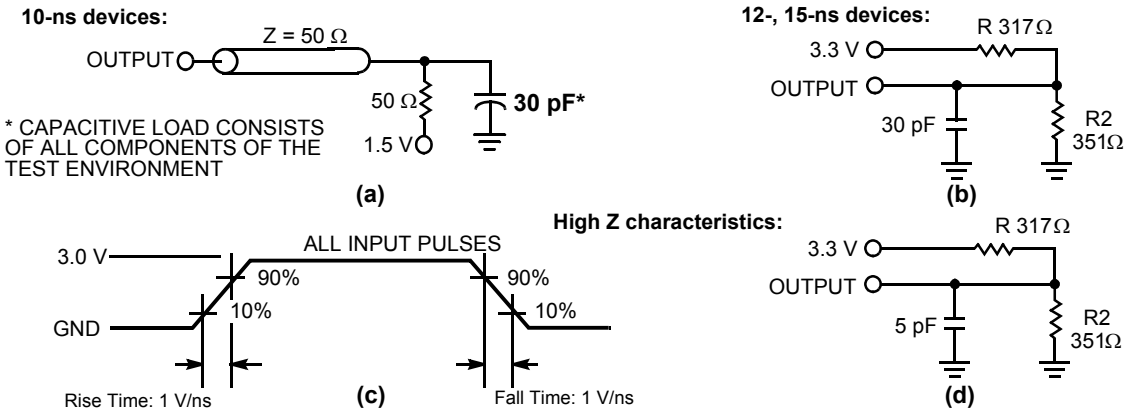
Parameter [3]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	T_A = 25 °C, f = 1 MHz, V_{CC} = 3.3 V	8	pF
C_{OUT}	Output capacitance		8	pF

Thermal Resistance

Parameter [3]	Description	Test Conditions	36-pin SOJ	44-pin TSOP II	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA / JESD51.	46.51	41.66	°C/W
Θ_{JC}	Thermal resistance (junction to case)		18.8	10.56	°C/W

AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms [4]



Notes
3. Tested initially and after any design or process changes that may affect these parameters.
4. AC characteristics (except High Z) for 10 ns parts are tested using the load conditions shown in Figure 3 (a). All other speeds are tested using the Thevenin load shown in Figure 3 (b). High Z characteristics are tested for all speeds using the test load shown in Figure 3 (d).

AC Switching Characteristics

Over the Operating Range

Parameter [5]	Description	-10		-12		-15		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle								
t_{power} [6]	V_{CC}(typical) to the first access	100	–	100	–	100	–	µs
t_{RC}	Read Cycle Time	10	–	12	–	15	–	ns
t_{AA}	Address to Data Valid	–	10	–	12	–	15	ns
t_{OHA}	Data Hold from Address Change	3	–	3	–	–	3	ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid	–	10	–	12	–	15	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid	–	5	–	6	–	7	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z [7]	0	–	0	–	0	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z [7, 8]	–	5	–	6	–	7	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z [7]	3	–	3	–	3	–	ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z [7, 8]	–	5	–	6	–	7	ns
t_{PU}	$\overline{CE}$ LOW to Power Up	0	–	0	–	0	–	ns
t_{PD}	$\overline{CE}$ HIGH to Power Down	–	10	–	12	–	15	ns
Write Cycle [9, 10]								
t_{WC}	Write Cycle Time	10	–	12	–	15	–	ns
t_{SCE}	$\overline{CE}$ LOW to Write End	7	–	8	–	10	–	ns
t_{AW}	Address Setup to Write End	7	–	8	–	10	–	ns
t_{HA}	Address Hold from Write End	0	–	0	–	0	–	ns
t_{SA}	Address Setup to Write Start	0	–	0	–	0	–	ns
t_{PWE}	$\overline{WE}$ Pulse Width	7	–	8	–	10	–	ns
t_{SD}	Data Setup to Write End	5	–	6	–	7	–	ns
t_{HD}	Data Hold from Write End	0	–	0	–	0	–	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z [7]	3	–	3	–	3	–	ns
t_{HZWE}	$\overline{WE}$ LOW to High Z [7, 8]	–	5	–	6	–	7	ns

Notes

5. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V.
6. t_{POWER} gives the minimum amount of time that the power supply should be at stable, typical V_{CC} values until the first memory access can be performed.
7. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
8. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of Figure 3 on page 5. Transition is measured ±500 mV from steady-state voltage.
9. The internal Write time of the memory is defined by the overlap of $\overline{CE}$ LOW, and $\overline{WE}$ LOW. $\overline{CE}$ and $\overline{WE}$ must be LOW to initiate a Write, and the transition of either of these signals can terminate the Write. The input data setup and hold timing should be referenced to the leading edge of the signal that terminates the Write.
10. The minimum Write cycle time for Write Cycle No. 2 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Waveforms

Figure 4. Read Cycle No. 1 (Address Transition Controlled) [11, 12]

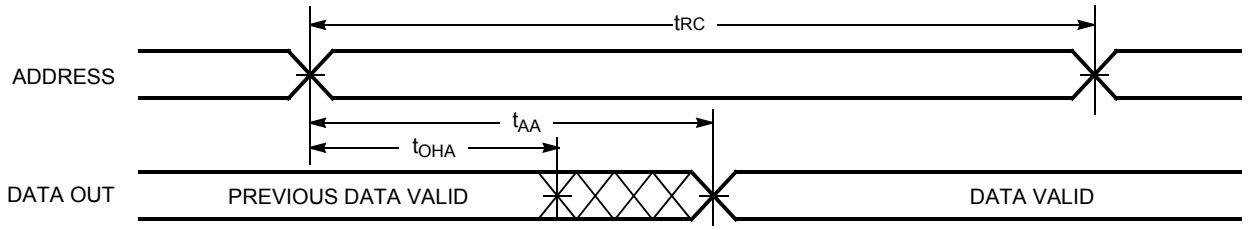


Figure 5. Read Cycle No. 2 ($\overline{OE}$ Controlled) [12, 13]

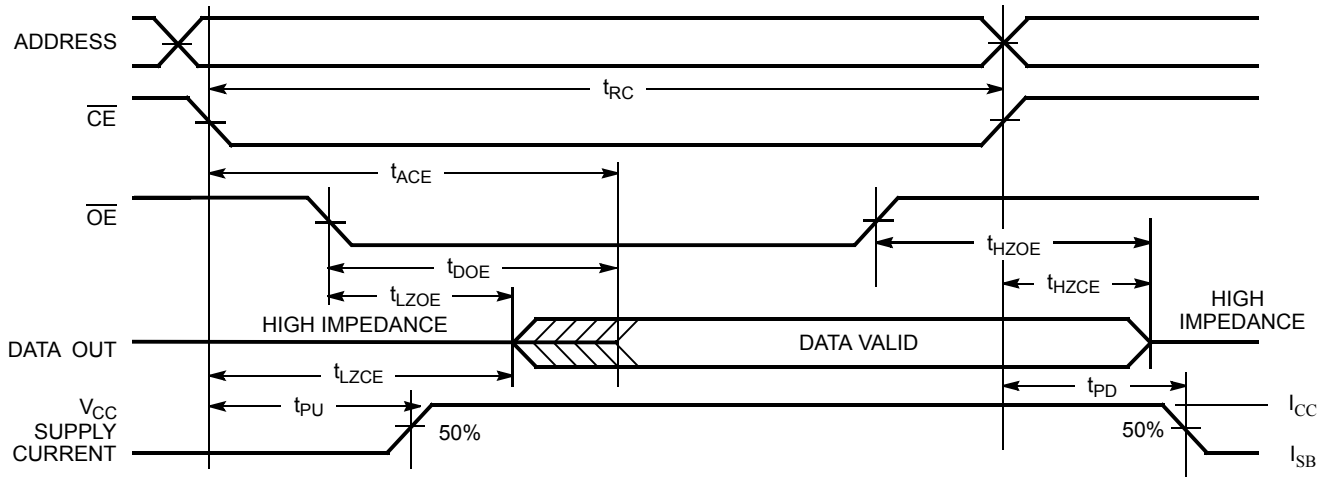
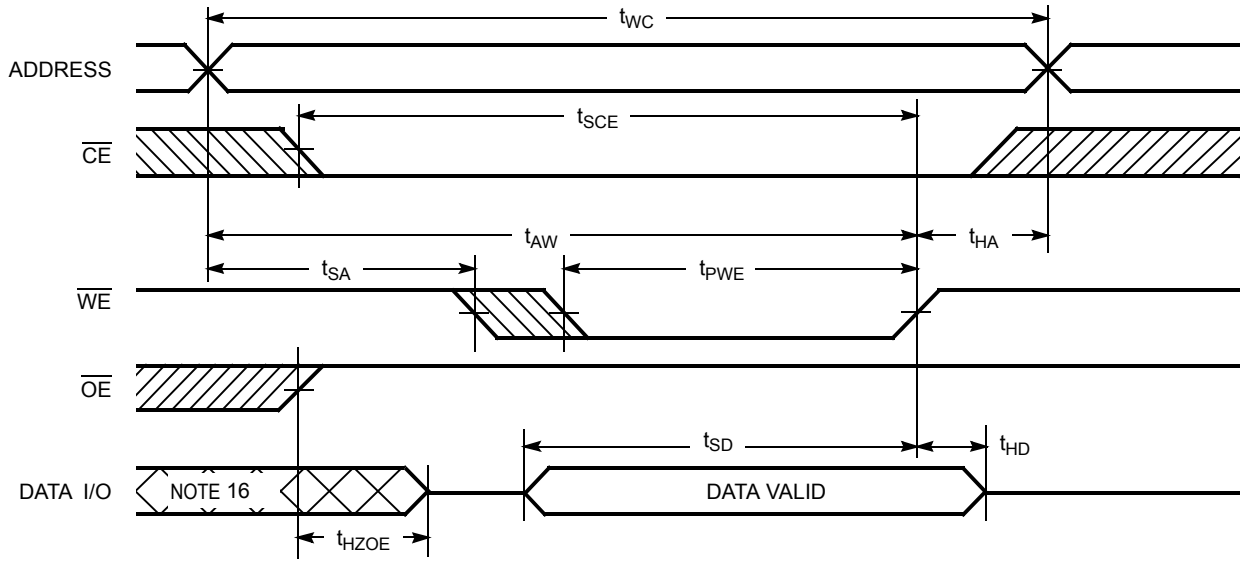


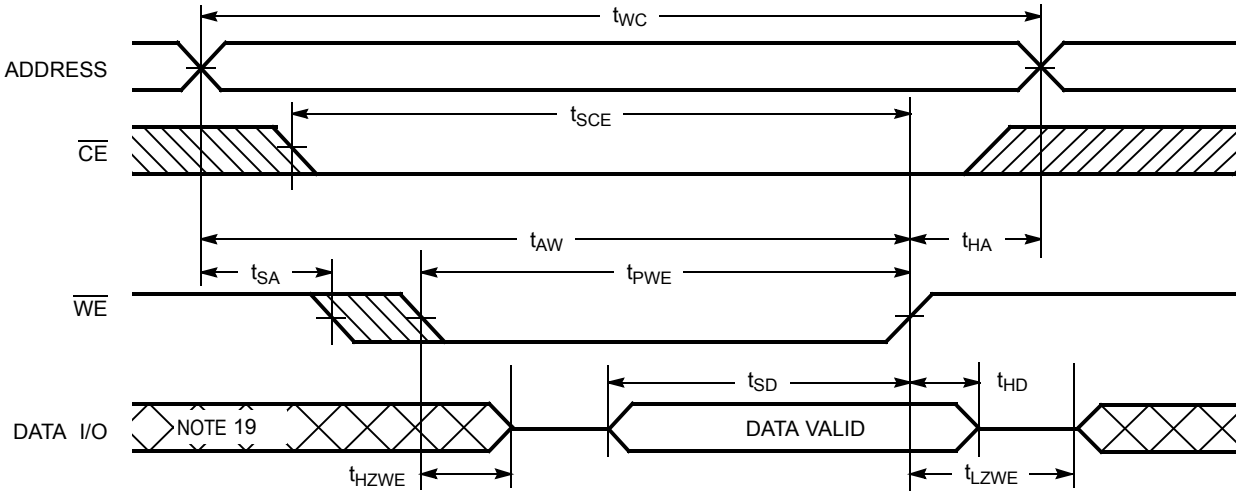
Figure 6. Write Cycle No. 1 ($\overline{WE}$ Controlled, $\overline{OE}$ HIGH During Write) [14, 15]



Notes
11. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
12. $\overline{WE}$ is HIGH for read cycles.
13. Address valid before or similar to $\overline{CE}$ transition LOW.
14. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
15. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in high impedance state.
16. During this period, the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 7. Write Cycle No. 2 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) [17, 18]



Notes
17. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in high impedance state.
18. The minimum Write cycle time for Write Cycle No. 2 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.
19. During this period, the I/Os are in output state. Do not apply input signals.

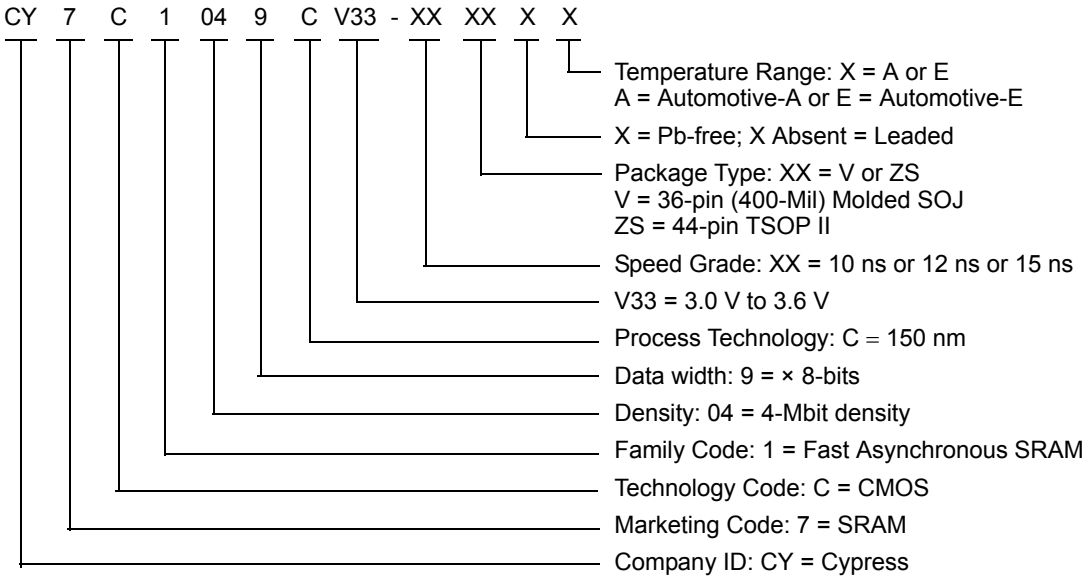
Truth Table

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O_0–I/O_7	Mode	Power
H	X	X	High Z	Power Down	Standby (I_{SB})
L	L	H	Data Out	Read	Active (I_{CC})
L	X	L	Data In	Write	Active (I_{CC})
L	H	H	High Z	Selected, Outputs Disabled	Active (I_{CC})

Ordering Information

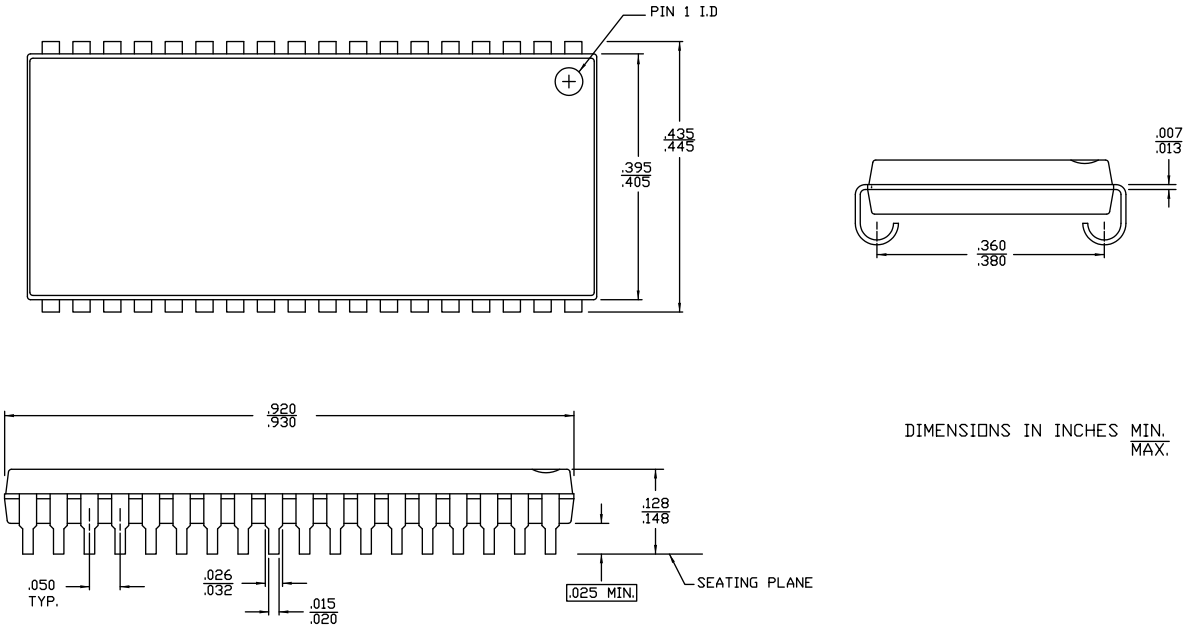
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1049CV33-10VXA	51-85090	36-pin (400-Mil) Molded SOJ (Pb-free)	Automotive-A
12	CY7C1049CV33-12ZSXA	51-85087	44-pin TSOP II (Pb-free)	Automotive-A
15	CY7C1049CV33-15VXE	51-85090	36-pin (400-Mil) Molded SOJ (Pb-free)	Automotive-E
	CY7C1049CV33-15ZSXE	51-85087	44-pin TSOP II (Pb-free)	Automotive-E

Ordering Code Definitions



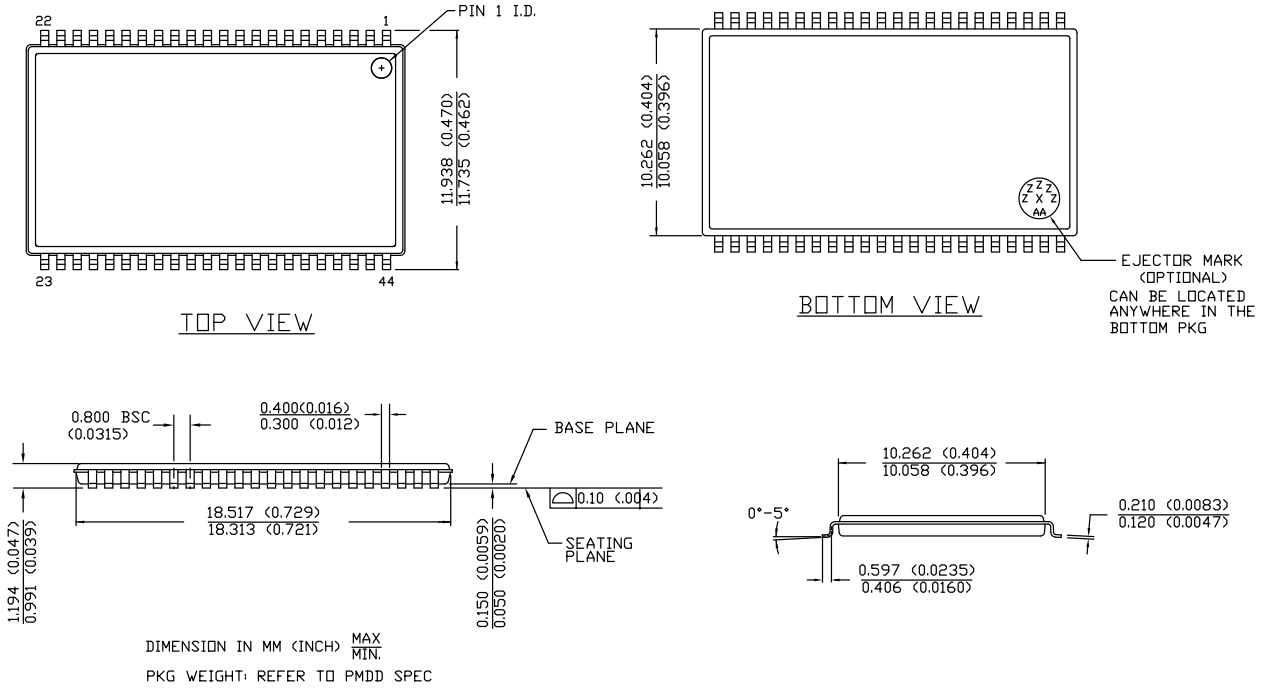
Package Diagrams

Figure 8. 36-pin SOJ V36.4 (Molded) Package Outline, 51-85090



Package Diagrams (continued)

Figure 9. 44-pin TSOP Z44-II Package Outline, 51-85087



Acronyms

Acronym	Description
$\overline{CE}$	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
$\overline{OE}$	Output Enable
SOJ	Small Outline J-lead
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
TTL	Transistor-Transistor Logic
$\overline{WE}$	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
µA	microampere
µs	microsecond
mA	milliampere
mm	millimeter
ms	millisecond
mW	milliwatt
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

Document History Page

Document Title: CY7C1049CV33 Automotive, 4-Mbit (512 K × 8) Static RAM Document Number: 001-67511				
Rev.	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	3186792	PRAS	03/03/2011	Separation of the automotive data sheet from CY7C1049CV33 spec no. 38-05006 Rev. *J. Further rev of 38-05006 would include only industrial / commercial parts.
*A	3265070	PRAS	05/24/2011	Updated Functional Description (Removed “For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.”). Updated in new template.
*B	3546915	NILE	03/09/2012	Updated Pin Definitions (Updated description of $\overline{WE}$ and $\overline{OE}$ pins). Updated Package Diagrams.
*C	4311615	NILE / VINI	03/21/2014	Updated Maximum Ratings: Added “Static discharge voltage” and “Latch up current” details. Updated AC Switching Characteristics: Updated Note 10. Updated Switching Waveforms: Added Note 18 and referred the same note in Figure 7. Updated Package Diagrams: spec 51-85087 – Changed revision from *D to *E. Updated in new template. Completing Sunset Review.

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